

Silicon Carbide Schottky Diode

Features

- 1200V Schottky Rectifier
- Zero Reverse Recovery Current
- High-Frequency Operation
- Temperature-Independent Switching Behavior
- Extremely Fast Switching

V_{RRM}	=	1200V
$I_F (T_C=150\text{ }^{\circ}\text{C})$	=	30A
Q_C	=	154 nC

Benefits

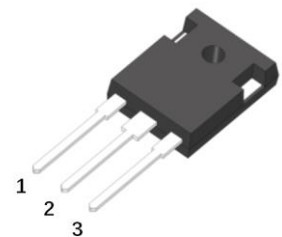
- Replace Bipolar with Unipolar Rectifiers
- Essentially No Switching Losses
- Higher Efficiency
- Reduction of Heat Sink Requirements
- Parallel Devices Without Thermal Runaway

Applications

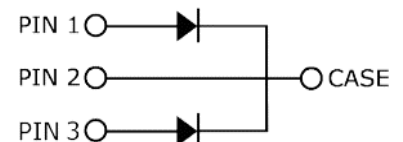
- Switch Mode Power Supplies (SMPS)
- Power Factor Correction
- Motor Drives

Package

TO-247-3L



Equivalent circuit



Maximum ratings (T_C=25°C unless otherwise specified)

Parameter	Symbol	Test Conditions	Value	Unit	Note
Repetitive Peak Reverse Voltage	V _{RRM}		1200	V	
DC Peak Reverse Voltage	V _R		1200	V	
Continuous Forward Current	I _F	T _C =25°C	91	A	Fig.3
		T _C =135°C	42		
		T _C =150°C	30		
Repetitive Peak Forward Surge Current	I _{FRM}	T _C =25°C, t _p =10 ms, Half Sine Pulse	135	A	
		T _C =110°C, t _p =10 ms, Half Sine Pulse	100		
Non-Repetitive Forward Surge Current	I _{FSM}	T _C =25°C, t _p =10 ms, Half Sine Pulse	190	A	
		T _C =110°C, t _p =10 ms, Half Sine Pulse	166		
Non-Repetitive Forward Surge Current	I _{F,MAX}	T _C =25°C, t _p =10μs, Square Wave Pulse	1120	A	
		T _C =110°C, t _p =10μs, Square Wave Pulse	930		
i ² t value	∫ i ² dt	T _C =25°C, t _p =10 ms	181	A ² s	
		T _C =110°C, t _p =10 ms	138		
Power Dissipation	P _{tot}	T _C =25°C	484	W	Fig.4
		T _C =110°C	210		
Operating Temperature	T _J		-55 to +175	°C	
Storage Temperature	T _{stg}		-55 to +175	°C	
TO-247 Mounting Torque		M3 Screw 6-32 Screw	1 8.8	Nm lbf-in	

Electrical Characteristics (T_J=25°C)

Parameter	Symbol	Test Conditions	Value			Unit	Note
			Min.	Typ.	Max.		
Forward Voltage	V _F	I _F =30A, T _J =25°C		1.50	1.8	V	Fig.1
		I _F =30A, T _J =175°C		2.00	3		
Reverse Current	I _R	V _R =1200V, T _J =25°C		15	250	μA	Fig.2
		V _R =1200V, T _J =175°C		208	450		
Total Capacitive Charge	Q _C	V _R =800V, T _J =25°C		154		nC	Fig.5
Total Capacitance	C	V _R =0V, T _J =25°C, f=1MHz		2425		pF	Fig.6
		V _R =400V, T _J =25°C, f=1MHz		138			
		V _R =800V, T _J =25°C, f=1MHz		133			
Capacitance Stored Energy	E _C	V _R =800 V		38		μJ	Fig.7

Thermal Characteristics

Parameter	Symbol	Value	Unit	Note
Thermal Resistance(Junction to Case)	R _{eJC}	0.31	°C/W	Fig. 8

Typical Performance

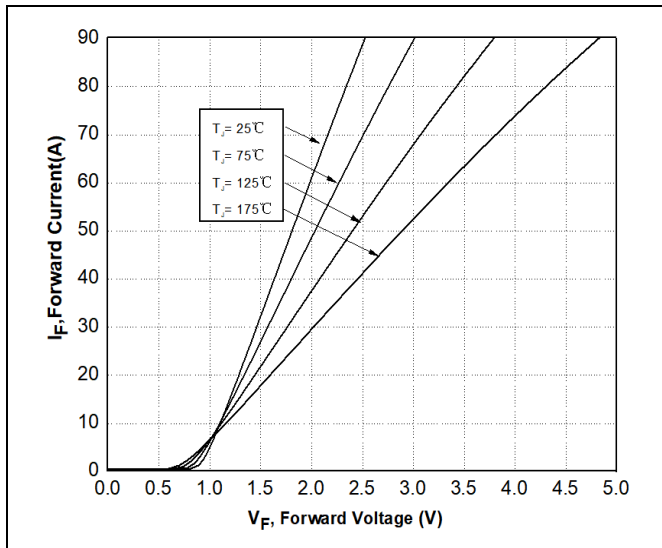


Figure 1. Forward Characteristics

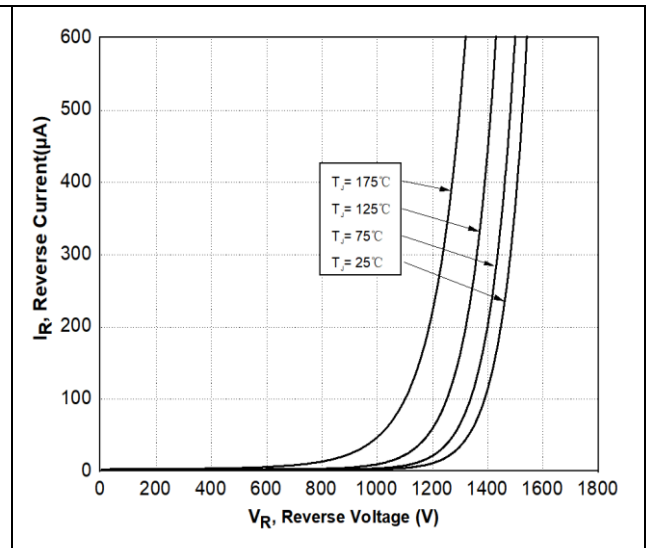


Figure 2. Reverse Characteristics

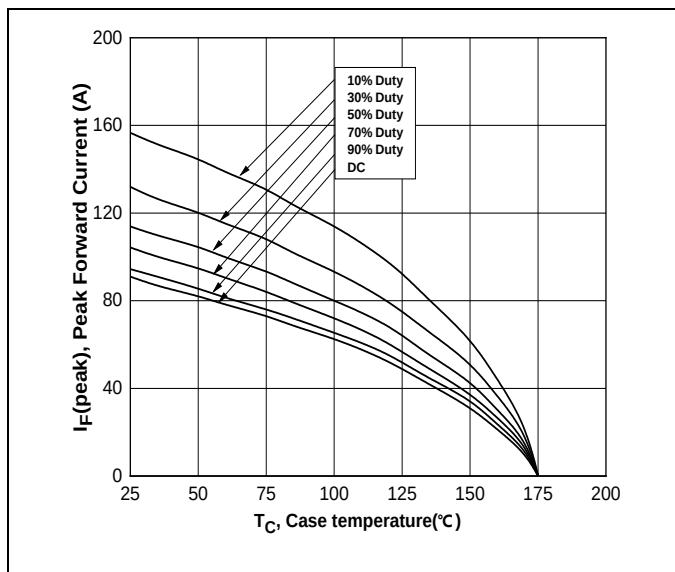


Figure 3. Current Derating

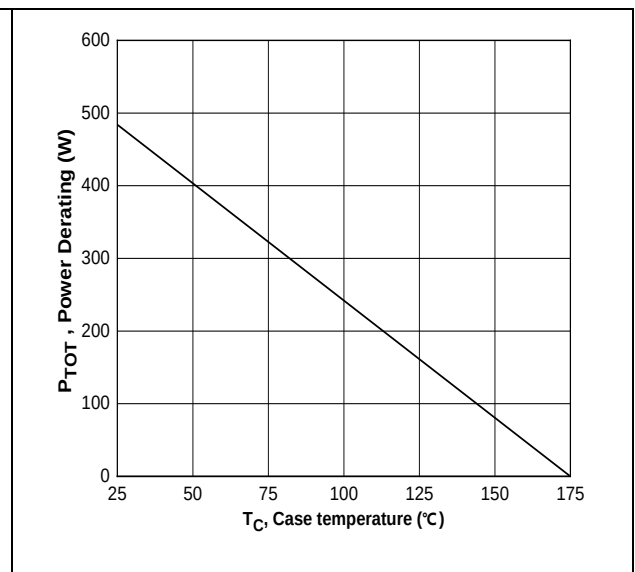


Figure 4. Power Derating

Typical Performance

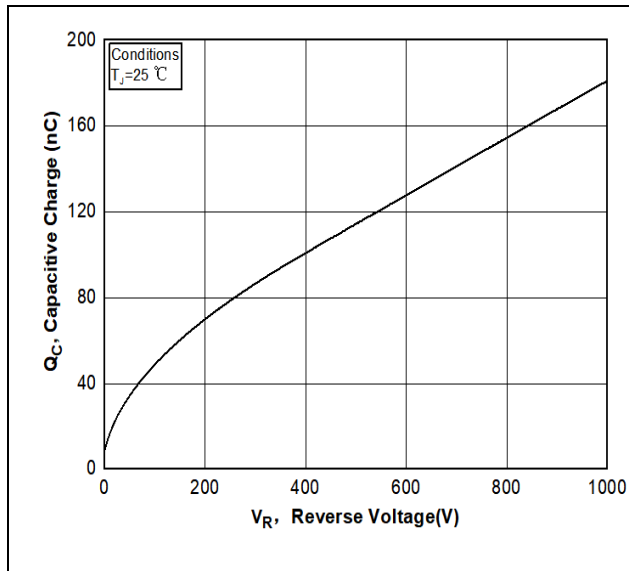


Figure 5. Capacitance Charge Vs. Reverse

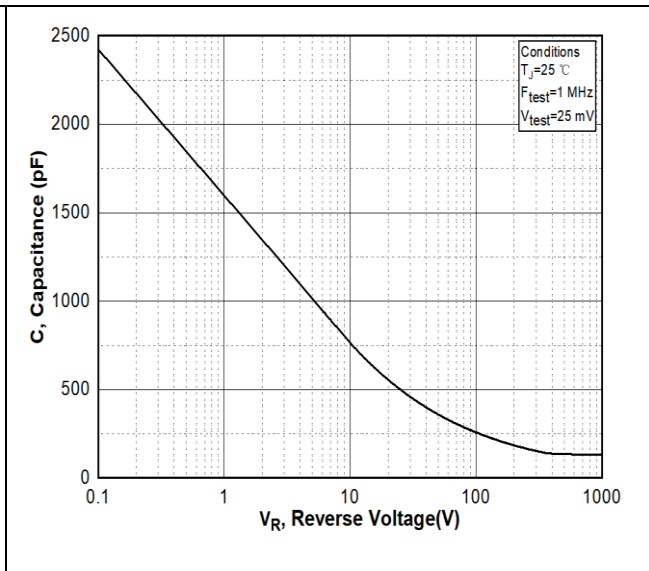


Figure 6. Capacitance Vs. Reverse Voltage

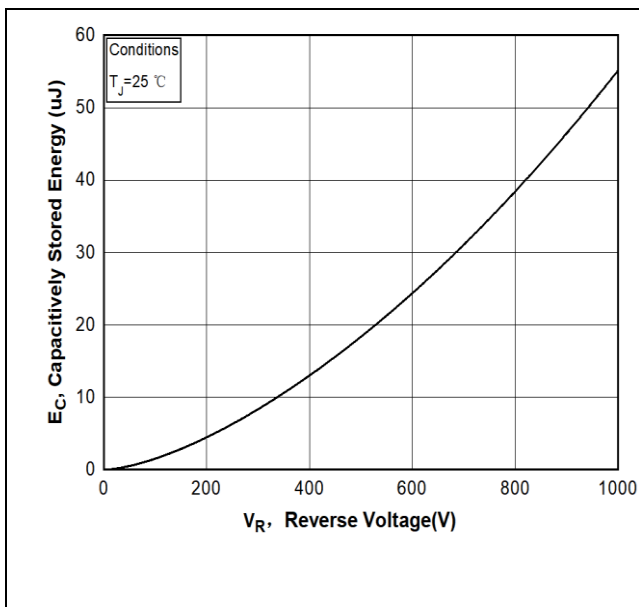


Figure 7. Capacitance Stored Energy

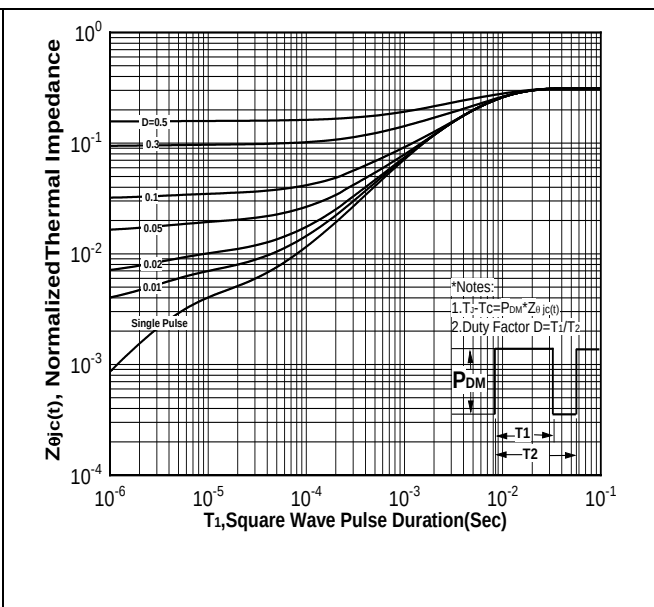


Figure 8. Transient Thermal Response Curve(Junction-to-Case)

Package Dimensions

Package TO-247-3L

